

10-25

Chapter 10

50, 57, 64, 66

Figure 25

At the top of $n=2$ band, each cell contains a whole wavelength. Thus $a = \lambda$.

At the top of the $n=1$ band, each cell contains one half wavelength, or $a = \lambda/2$.

The Energy is $E = \frac{\hbar^2 k^2}{2m}$

The energy at the top of the $n=2$

$$E_{\text{top}} = \frac{\hbar^2}{2m} \left(\frac{2\pi}{a} \right)^2$$

$$k = \frac{n\pi}{a}$$

$$E_{\text{top}} = \frac{\hbar^2}{2m} \left(\frac{2\pi}{2a} \right)^2$$

$$\Delta E = E_{\text{top}} - E_{\text{top}} = \frac{\hbar^2 (2\pi/a)^2}{2m} - \frac{\hbar^2 (2\pi/2a)^2}{2m}$$

$$= \frac{3\hbar^2 \pi^2}{2ma^2}$$

$$\Delta E = \frac{3 (1.055 \times 10^{-34} \text{ Js})^2 \pi^2}{2 (9.11 \times 10^{-31} \text{ kg}) (0.15 \times 10^{-9} \text{ m})^2}$$

$$\Delta E \approx 50 \text{ eV}$$

(57)

Semiconductor

Gap 1eV

$\Delta T = 4K$

Show that σ ~~is~~ by 30%

Conductivity is dominated by a factor of $e^{-E_{gap}/2k_B T}$

$$\frac{\sigma_f}{\sigma_i} = \exp \left[\frac{-E_{gap}}{2k_B} \left[\frac{1}{T_f} - \frac{1}{T_i} \right] \right]$$
$$= \exp \left[\frac{E_{gap} (T_f - T_i)}{2k_B T_f T_i} \right]$$

$$= \exp \left[\frac{(1.6 \times 10^{-19} J)(4K)}{2(1.38 \times 10^{-23} J/K)(295)(299)} \right]$$

$$= 1.3 \sim 30\% \text{ rise}$$

64

$$E = \frac{hc}{\lambda} = \frac{1240 \text{ eV} \cdot \text{nm}}{700 \text{ nm}}$$

$$E = 1.77 \text{ eV}$$

56

$$E = \frac{hc}{\lambda}$$

$$\lambda = \frac{hc}{E} = \frac{1240 \text{ eV} \cdot \text{nm}}{2.25 \text{ eV}}$$

$$\lambda = 551 \text{ nm}$$